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FIRST NAMED INVENTOR: Xiaojun Weng et al.
TITLE: Narrow Energy Band Gap Gallium Arsenide
Nitride Semi-Conductors And An Ion-Cut-Synthesis
Method For Producing The Same

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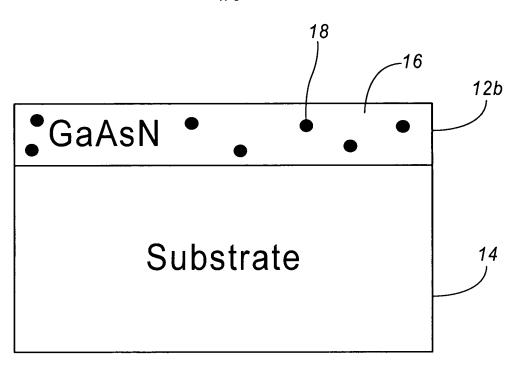


FIG. 1

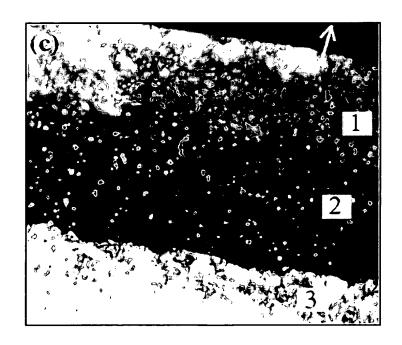


FIG. 2a

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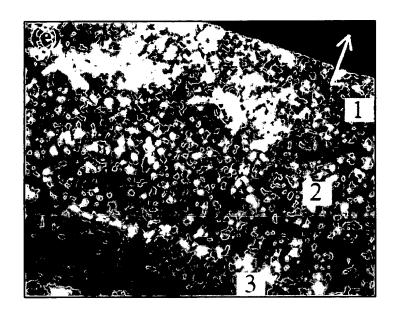


FIG. 2b

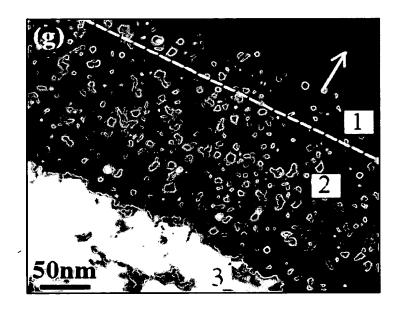


FIG. 2c

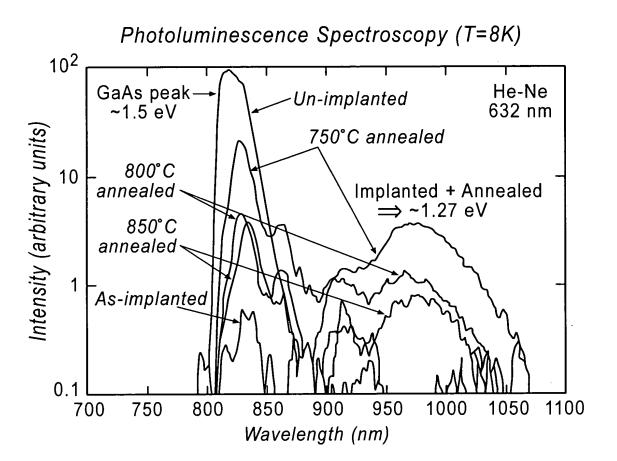
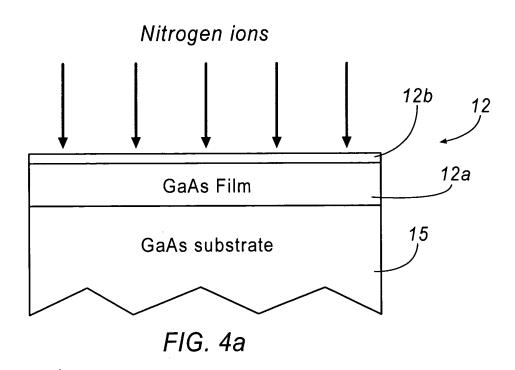
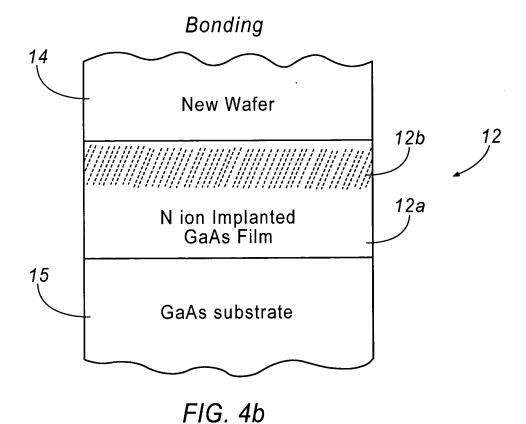


FIG. 3

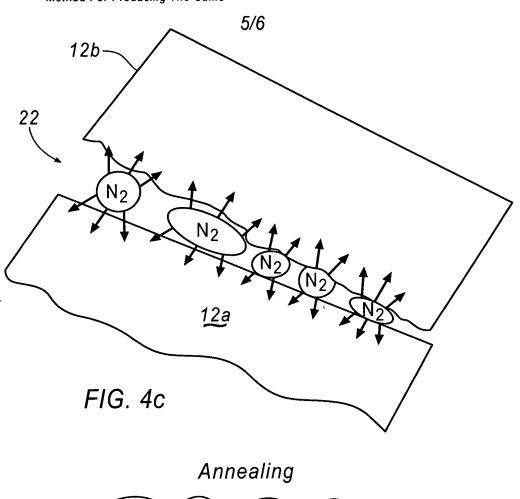
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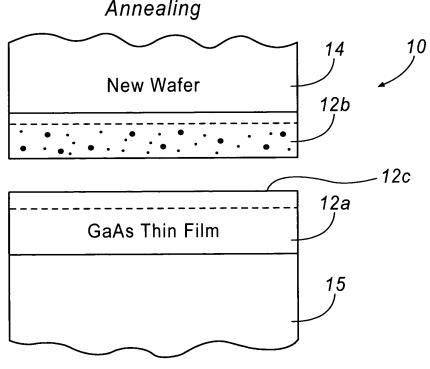


FIG. 4d

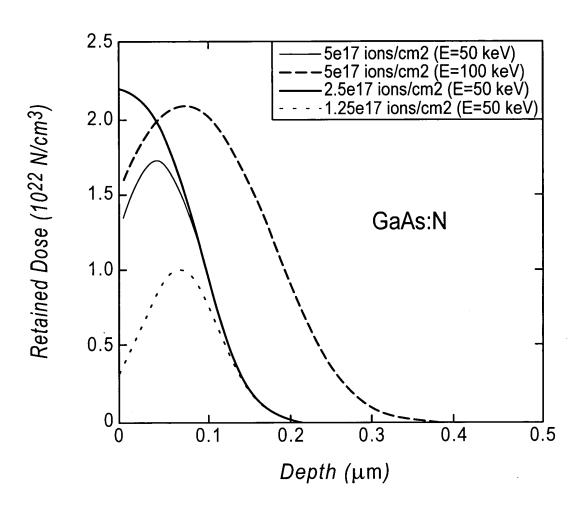


FIG. 5